

isc Silicon PNP Darlington Power Transistor

BDX54C

DESCRIPTION

- Collector-Emitter Sustaining Voltage-
: $V_{CE(sus)} = -100V(\text{Min})$
- High DC Current Gain
: $h_{FE} = 750(\text{Min}) @ I_C = -3A$
- Low Collector Saturation Voltage
: $V_{CE(sat)} = -2.0 V (\text{Max}) @ I_C = -3.0 A$
- Complement to Type BDX53C

APPLICATIONS

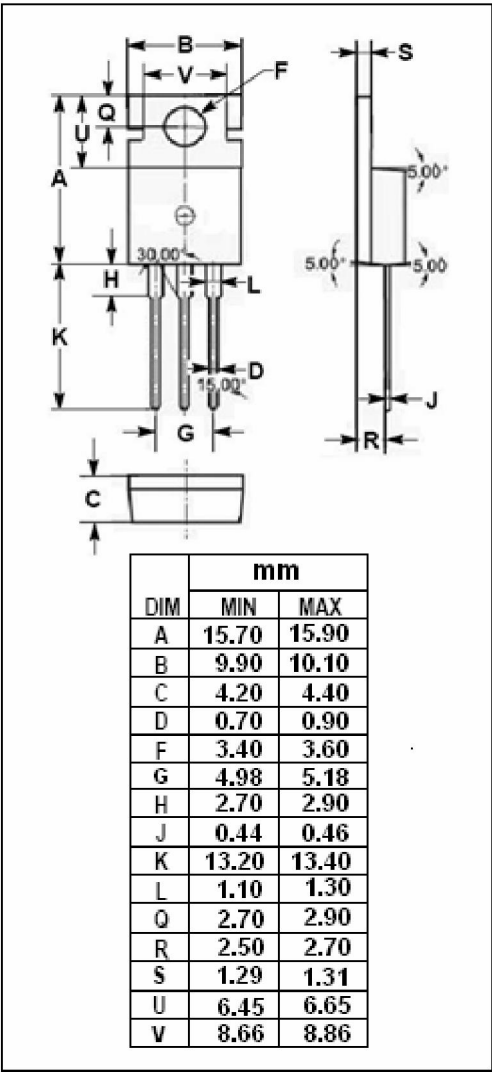
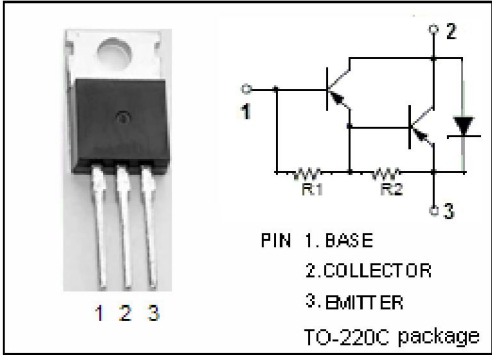
- Designed for general-purpose amplifier and low-speed switching applications.

ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-100	V
V_{CEO}	Collector-Emitter Voltage	-100	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-8	A
I_{CP}	Collector Current-Peak	-12	A
I_B	Base Current-Continuous	-0.2	A
P_C	Collector Power Dissipation @ $T_C=25^{\circ}C$	65	W
T_J	Junction Temperature	150	$^{\circ}C$
T_{stg}	Storage Temperature Range	-65~150	$^{\circ}C$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th j-c}$	Thermal Resistance,Junction to Case	1.92	$^{\circ}C/W$
$R_{th j-a}$	Thermal Resistance,Junction to Ambient	70	$^{\circ}C/W$



isc Silicon PNP Darlington Power Transistor**BDX54C****ELECTRICAL CHARACTERISTICS****T_C=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(SUS)}	Collector-Emitter Breakdown Voltage	I _C = -100mA; I _B = 0	-100			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = -3A; I _B = -12mA			-2.0	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = -3A; I _B = -12mA			-2.5	V
I _{CBO}	Collector Cutoff Current	V _{CB} = -100V; I _E = 0			-0.2	mA
I _{CEO}	Collector Cutoff Current	V _{CE} = -50V; I _B = 0			-0.5	mA
I _{EBO}	Emitter Cutoff Current	V _{EB} = -5V; I _C = 0			-2	mA
h _{FE}	DC Current Gain	I _C = -3A ; V _{CE} = -3V	750			
C _{OB}	Output Capacitance	I _E = 0; V _{CB} = -10V, f _{test} = 0.1MHz			200	pF